

Ke Zou

List of Publications by Year in descending order

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34
papers

1,883
citations

430874

18
h-index

395702

33
g-index

35
all docs

35
docs citations

35
times ranked

3374
citing authors

#	ARTICLE	IF	CITATIONS
1	Reversible fluorination of graphene: Evidence of a two-dimensional wide bandgap semiconductor. Physical Review B, 2010, 81, .	3.2	365
2	High-Mobility Few-Layer Graphene Field Effect Transistors Fabricated on Epitaxial Ferroelectric Gate Oxides. Physical Review Letters, 2009, 102, 136808.	7.8	197
3	Deposition of High-Quality HfO_2 on Graphene and the Effect of Remote Oxide Phonon Scattering. Physical Review Letters, 2010, 105, 126601.	7.8	155
4	Unusual resistance hysteresis in n-layer graphene field effect transistors fabricated on ferroelectric $\text{Pb}(\text{Zr}_{0.2}\text{Ti}_{0.8})\text{O}_3$. Applied Physics Letters, 2010, 97, .	3.3	115
5	Evidence for Spin-Flip Scattering and Local Moments in Dilute Fluorinated Graphene. Physical Review Letters, 2012, 108, 226602.	7.8	115
6	Transport Studies of Dual-Gated ABC and ABA Trilayer Graphene: Band Gap Opening and Band Structure Tuning in Very Large Perpendicular Electric Fields. Nano Letters, 2013, 13, 369-373.	9.1	109
7	Quantum scattering time and its implications on scattering sources in graphene. Physical Review B, 2009, 80, .	3.2	107
8	Effective mass of electrons and holes in bilayer graphene: Electron-hole asymmetry and electron-electron interaction. Physical Review B, 2011, 84, .	3.2	104
9	$\text{LaTiO}_3/\text{KTaO}_3$ interfaces: A new two-dimensional electron gas system. APL Materials, 2015, 3, .	5.1	94
10	Transport in gapped bilayer graphene: The role of potential fluctuations. Physical Review B, 2010, 82, .	3.2	85
11	Mechanism for Current Saturation and Energy Dissipation in Graphene Transistors. Physical Review Letters, 2010, 104, 236601.	7.8	76
12	Multiferroic tunnel junctions. Frontiers of Physics, 2012, 7, 380-385.	5.0	41
13	Role of double TiO_2 layers at the interface of $\text{FeSe}/\text{SrTiO}_3$ superconductors.	3.2	40
14	Integrating functional oxides with graphene. Solid State Communications, 2012, 152, 1365-1374.	1.9	37
15	Robust ferromagnetism in wafer-scale monolayer and multilayer Fe_3GeTe_2 . Npj 2D Materials and Applications, 2020, 4, .	7.9	37
16	Surface phase, morphology, and charge distribution transitions on vacuum and ambient annealed SrTiO_3 (100). Physical Review B, 2016, 93, .		34
17	A high density two-dimensional electron gas in an oxide heterostructure on Si (001). APL Materials, 2014, 2, 116109.	5.1	29
18	Picoscale structural insight into superconductivity of monolayer $\text{FeSe}/\text{SrTiO}_3$. Science Advances, 2020, 6, eaay4517.	10.3	24

#	ARTICLE	IF	CITATIONS
19	Effective mass in bilayer graphene at low carrier densities: The role of potential disorder and electron-electron interaction. <i>Physical Review B</i> , 2016, 94, .	3.2	16
20	Tuning stoichiometry and its impact on superconductivity of monolayer and multilayer FeSe on SrTiO_3 . <i>Physical Review B</i> , 2020, 101, .		16
21	Single-crystalline epitaxial TiO film: A metal and superconductor, similar to Ti metal. <i>Science Advances</i> , 2021, 7, .	10.3	14
22	High-temperature superconductivity and its robustness against magnetic polarization in monolayer FeSe on EuTiO_3 . <i>Npj Quantum Materials</i> , 2021, 6, .	5.2	14
23	High-order replica bands in monolayer FeSe/ SrTiO_3 revealed by polarization-dependent photoemission spectroscopy. <i>Nature Communications</i> , 2021, 12, 4573.	12.8	11
24	Revealing surface-state transport in ultrathin topological crystalline insulator SnTe films. <i>APL Materials</i> , 2019, 7, .	5.1	9
25	Epitaxial growth of perovskite SrBiO_3 film on SrTiO_3 . <i>Physical Review Materials</i> , 2019, 2, .	2.4	9
26	Controlling the electrical and magnetic ground states by doping in the complete phase diagram of titanate EuTiO_3 thin films. <i>Physical Review B</i> , 2020, 101, .	3.2	7
27	Length Scale and Dimensionality of Defects in Epitaxial SnTe Topological Crystalline Insulator Films. <i>Advanced Materials Interfaces</i> , 2017, 4, 1601011.	3.7	6
28	Weak antilocalization in topological crystalline insulator SnTe films deposited using amorphous seeding on SrTiO_3 . <i>APL Materials</i> , 2021, 9, .	5.1	4
29	Hong <i>et al.</i> Reply. <i>Physical Review Letters</i> , 2012, 109, .	7.8	3
30	Electronic properties of epitaxial $\text{La}_{1-x}\text{Sr}_x\text{RhO}_3$ thin films. <i>Physical Review B</i> , 2021, 103, .	3.2	3
31	Suppression of the spectral weight of topological surface states on the nanoscale via local symmetry breaking. <i>Physical Review Materials</i> , 2018, 2, .	2.4	3
32	Hydrogen Atom Doping: A Versatile Method for Modulated Interface Resistive Switching. <i>Advanced Electronic Materials</i> , 0, , 2200353.	5.1	2
33	Crystalline Insulators: Length Scale and Dimensionality of Defects in Epitaxial SnTe Topological Crystalline Insulator Films (<i>Adv. Mater. Interfaces</i> 2/2017). <i>Advanced Materials Interfaces</i> , 2017, 4, .	3.7	1
34	Identifying crystal structures and chemical reactions at the interface of stanene on Bi_2Te_3 . <i>Journal of Applied Physics</i> , 2020, 128, .	2.5	1